

GENERAL DESCRIPTION

Glass passivated high commutation triacs in a plastic envelope intended for use in circuits where high static and dynamic dV/dt and high di/dt can occur loads. These devices will commutate the full rated rms current at the maximum rated junction temperature, without the aid of a snubber.

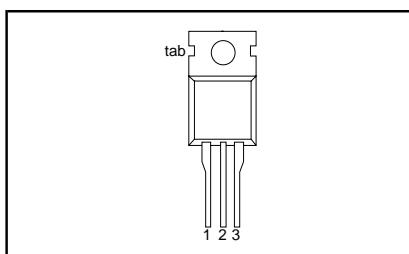
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{DRM}	BTA225- Repetitive peak off-state voltages	500B	600B	800B	V
$I_{T(RMS)}$	RMS on-state current	500	600	800	A
I_{TSM}	Non-repetitive peak on-state current	25	25	25	A
		190	190	190	A

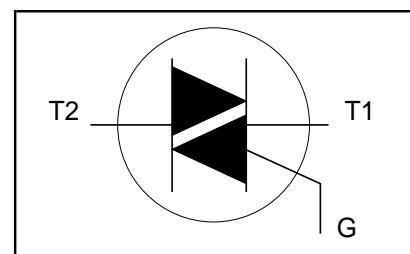
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
V_{DRM}	Repetitive peak off-state voltages		-	-500	-600	-800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 91^\circ C$	-	600 ¹	600 ¹	800	A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25^\circ C$ prior to surge	-	25			
I^2t dl_T/dt	I^2t for fusing Repetitive rate of rise of on-state current after triggering	t = 20 ms t = 16.7 ms t = 10 ms $I_{TM} = 30 A$; $I_G = 0.2 A$; $dl_G/dt = 0.2 A/\mu s$	- - - -	190 209 180 100			A A A ² s A/ μs
I_{GM} V_{GM} P_{GM} $P_{G(AV)}$	Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms period	- - - -	2 5 5 0.5			A V W W
T_{stg} T_j	Storage temperature Operating junction temperature		-40	150 125			°C °C

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ μs .

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base	full cycle	-	-	1.0	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	half cycle in free air	-	60	1.4	K/W

STATIC CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{GT}	Gate trigger current ²	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G-	2	18	50	mA
I_L	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G-	2	21	50	mA
I_H	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	34	50	mA
V_T	On-state voltage	$I_T = 30\text{ A}$	-	31	60	mA
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	34	90	mA
I_D	Off-state leakage current	$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125^\circ\text{C}$ $V_D = V_{DRM(\max)}; T_j = 125^\circ\text{C}$	0.25	0.7	1.55	V
			-	0.4	1.5	V
			-	0.1	0.5	mA

DYNAMIC CHARACTERISTICS

$T_j = 25^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(\max)}; T_j = 125^\circ\text{C};$ exponential waveform; gate open circuit	1000	4000	-	V/ μs
dl_{com}/dt	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}; T_j = 125^\circ\text{C}; I_{T(RMS)} = 25\text{ A};$ without snubber; gate open circuit	-	44	-	A/ms
t_{gt}	Gate controlled turn-on time	$I_{TM} = 30\text{ A}; V_D = V_{DRM(\max)}; I_G = 0.1\text{ A};$ $dl_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	μs

² Device does not trigger in the T2-, G+ quadrant.

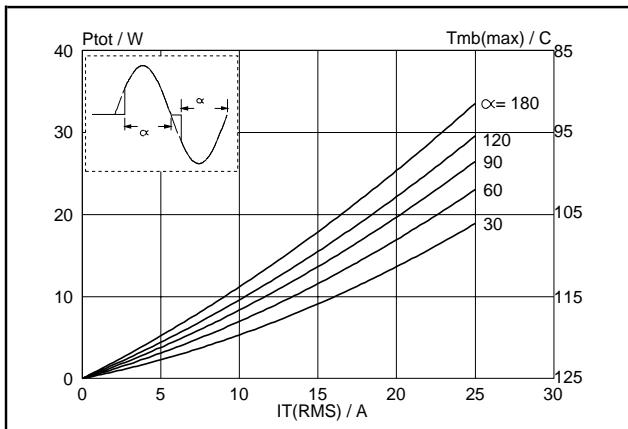


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

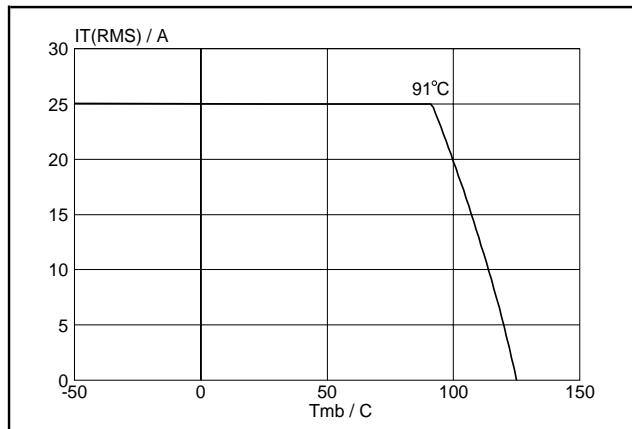


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus mounting base temperature T_{mb} .

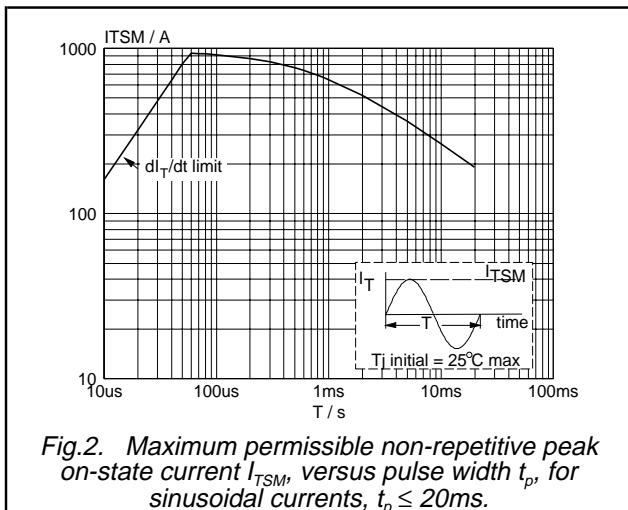


Fig.2. Maximum permissible non-repetitive peak on-state current $I_{TS(M)}$, versus pulse width t_p , for sinusoidal currents, $t_p \leq 20\text{ms}$.

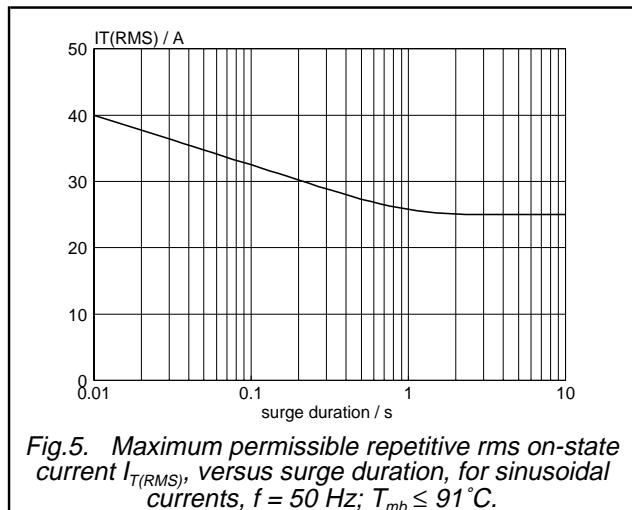


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, $f = 50\text{ Hz}$; $T_{mb} \leq 91^\circ\text{C}$.

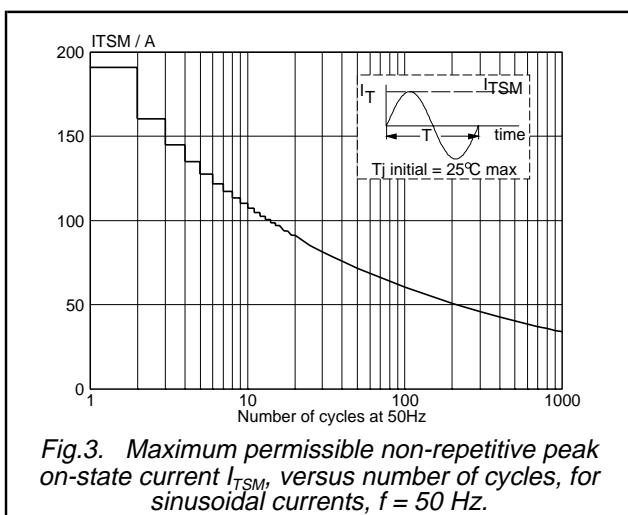


Fig.3. Maximum permissible non-repetitive peak on-state current $I_{TS(M)}$, versus number of cycles, for sinusoidal currents, $f = 50\text{ Hz}$.

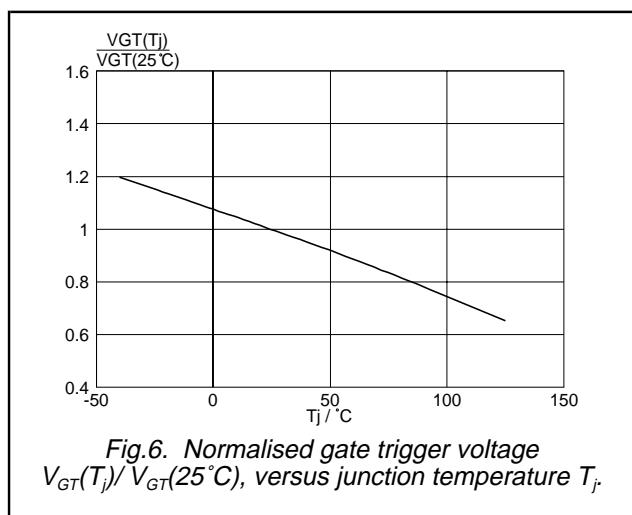


Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^\circ\text{C})$, versus junction temperature T_j .

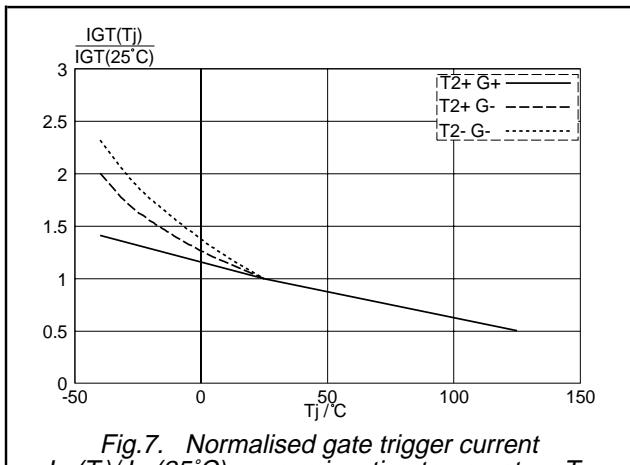


Fig.7. Normalised gate trigger current $I_{GT}(T_j)/I_{GT}(25^\circ C)$, versus junction temperature T_j .

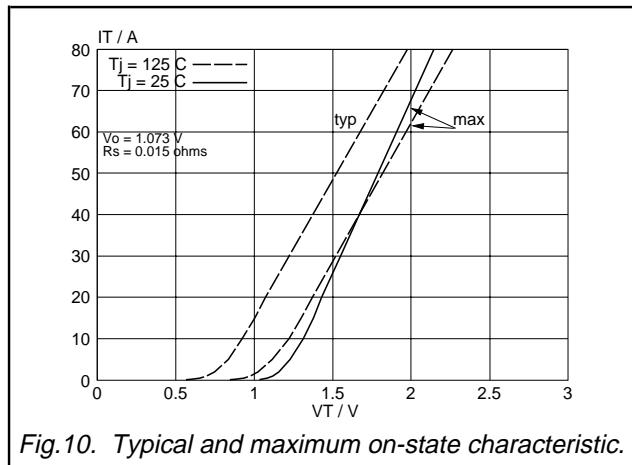


Fig.10. Typical and maximum on-state characteristic.

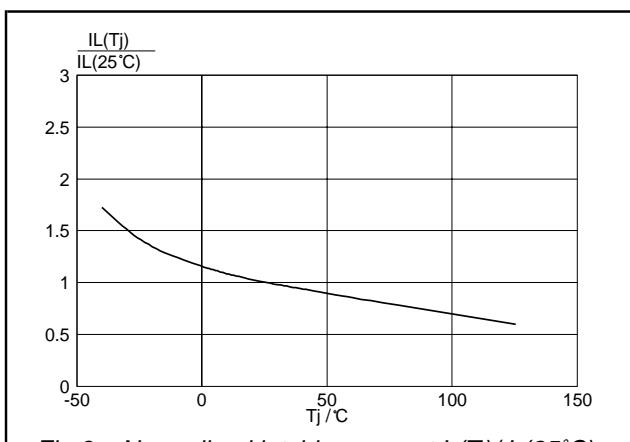


Fig.8. Normalised latching current $I_L(T_j)/I_L(25^\circ C)$, versus junction temperature T_j .

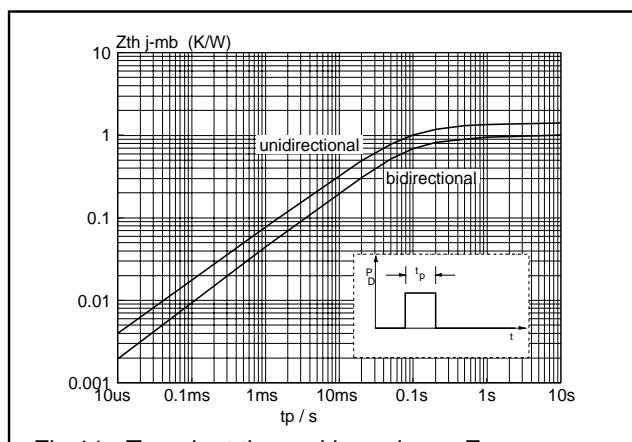


Fig.11. Transient thermal impedance $Z_{th,j-mb}$, versus pulse width t_p .

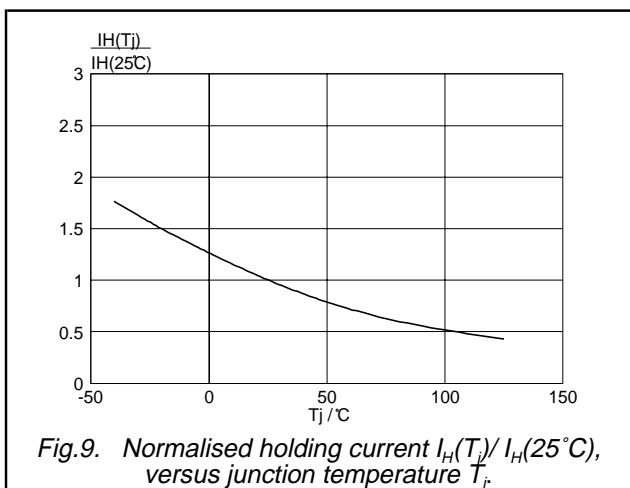


Fig.9. Normalised holding current $I_H(T_j)/I_H(25^\circ C)$, versus junction temperature T_j .

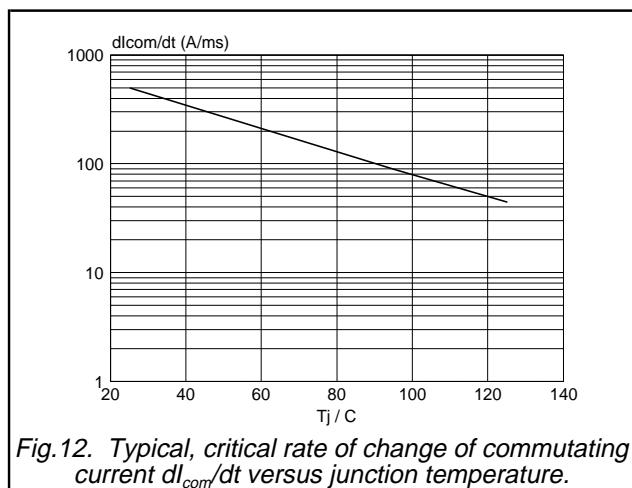


Fig.12. Typical, critical rate of change of commutating current dl_{com}/dt versus junction temperature.

Dimensions in mm

Net Mass: 2 g

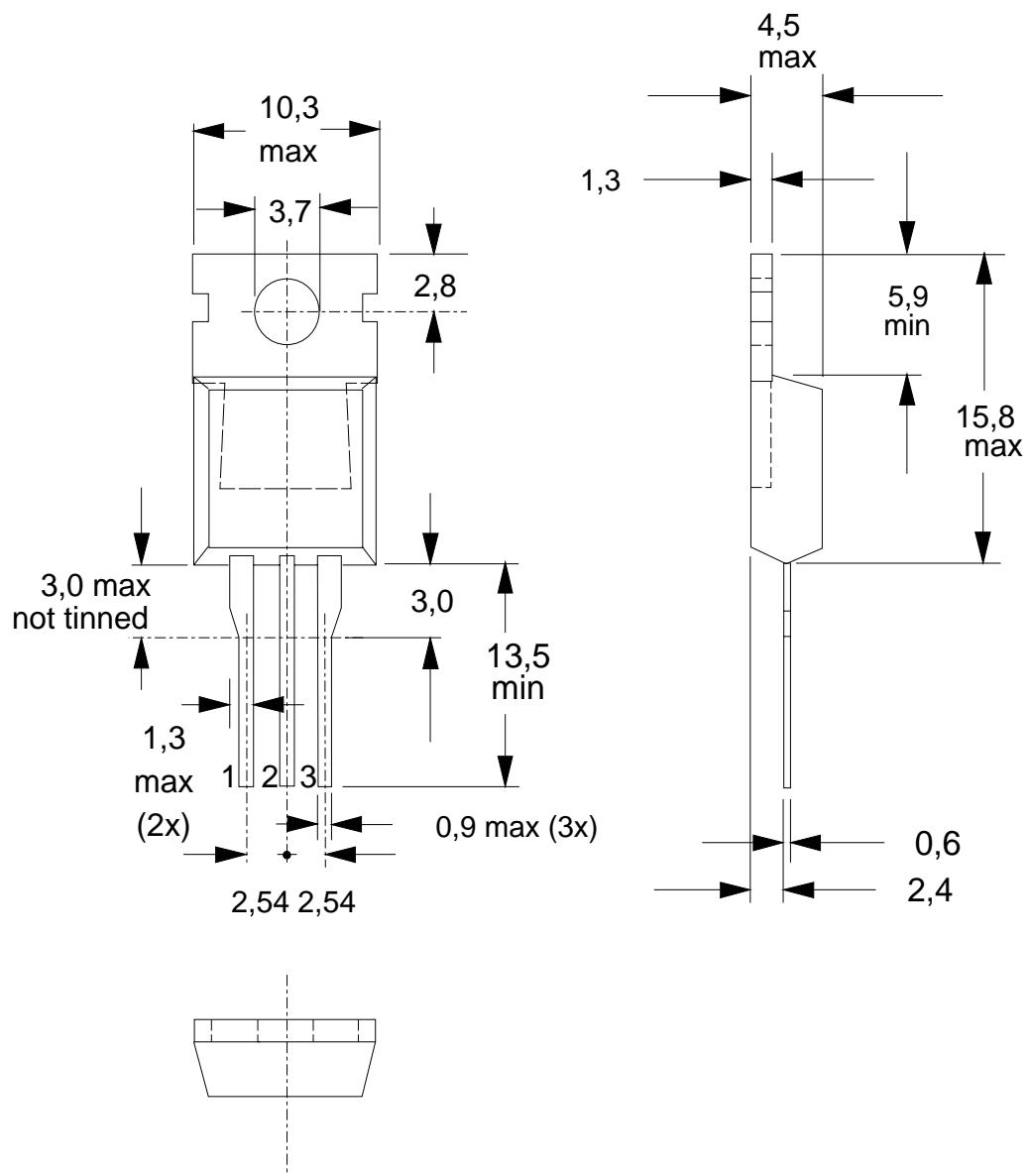


Fig.13. TO220AB; pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".